NMAM INSTITUTE OF TECHNOLOGY, NITTE Off-Campus Centre of Nitte (Deemed to be University) Second Semester B.Tech (CBCS) Degree Examinations CY1003-1-MATERIALS CHEMISTRY FOR COMPUTER SYSTEMS

MULTIPLE CHOICE QUESTIONS: UNIT - II

Sensors, PCB & Nanomaterials

١.	analytically useful signal.					
				T		
	A)	Chemical	B)	Physical		
_	C)	Electrical	D)	Mechanical		
Ans	C)	Electrical				
2.	The s	sensors that are used to monitor the concen	ıtrati	ons of chemical substances are called as		
	A)	Chemical Sensor	B)	Physical Sensor		
	C)	Mechanical Sensor	D)	Concentration Sensor		
Ans	A)	Chemical Sensor				
3.		· · · · · · · · · · · · · · · · · · ·	-	nent that converts chemical reactions into		
	meas	urable electrical signals is called as		·		
	A)	Receptor	B)	Amplifier		
	C)	Detector	D)	Transducer		
Ans	D)	Transducer				
4.	The r	role of the electrode in an electrochemical se	ensc	or is it acts like		
	A)	a modifier	B)	an amplifier		
	C)	a transducer	D)	a detector		
Ans	C)	a transducer	•			
5.	The c	cathode which is used in the electrochemica	al se	nsing of Dissolved oxygen (DO) is		
	A)	MWCNT	B)	Glucose Oxidase		
	C)	Ag	D)	rGO		
Ans	C)	Ag				
6.	Elect	ectrochemical DO sensors are an example of				
	A)	Potentiometric Sensor	B)	Amperometric Sensor		
	C)	Conductometric Sensor	D)	Colorimetric Sensor		
Ans	B)	Amperometric sensor				
7.	Elect	lectrochemical DO sensors are also called as				
	A)	Clark type sensor	B)	Spark type sensor		
	C)	Click type sensor	D)	Stack type sensor		
Ans	A)	Clark type sensor				
8.	The anode used in the Electrochemical DO sensor is					
	A)	Au	B)	Ag		
	C)	Pt	D)	Zn		
Ans	D)	Zn				
9.		sensing layer of the optical DO sensor conta				
	A)	Aromatic hydrocarbons	B)	Polycyclic hydrocarbons		
	C)	Fluorescent dyes	D)	Congo red dye		
Ans	C)	<i>j</i>				
10.	The solid electrolyte that is used in the electrochemical gas sensing of SO _x is					
	A)	KOH	B)	NaOH		

	C)	K ₂ SO ₄	D)	H ₂ SO ₄		
	C)	K ₂ SO ₄				
11.	The r	The reference electrode used in the electrochemical gas sensing of NO _x is				
	A)	Ag/AgCl	B)	Zn/ZnCl ₂		
	C)	Fe/FeCl ₂	D)	Cu/CuSO ₄		
Ans	A)	Ag/AgCI				
12.	In the	e electrochemical sensing of NO _x , the worki	ng el	ectrode glassy carbon electrode will be		
	modi	fied with				
	A)	MWCNT-Ag@Pt	B)	rGo-Co₃O₄@Pt		
	C)	rGo-Co₃O₄@Ag	D)	rGo-MWCNT@Pt		
Ans	B)	rGo-Co₃O₄@Pt				
13.	What	is the function of a transducer in an electro	che	mical sensor?		
	A)	To convert the reaction into measurable	B)	To convert the reaction into a measurable		
		potential.		electrical signal		
	C)	To convert the reaction into an optical signal	D)	To convert the reaction output into a mechanical		
				displacement		
Ans	B)	To convert the reaction into a measurable				
14.			desiç	gned to detect and convert incident light rays		
		electrical signals.				
	A)	Conductometric sensors	B)	Thermometric sensors		
	C)	Optical sensors	D)	Electrochemical sensors		
Ans	C)	Optical sensors				
15.		type of coating is used to conne				
	A)	Electroplating	B)	Organic Coating		
	C)	Electroless Plating	D)	Inorganic Coating		
Ans	C)	Electroless Plating				
16.		full form of PCB is				
	A)	Polished Circuit Board	B)	Printed Circuit Board		
_	C)	Polymer Circuit Board	D)	Printed Circular Board		
Ans	B)	Printed Circuit Board				
17.		electroless plating, the surface of the subs				
	A)	SnCl ₂ and PdCl ₂	B)	Alkali		
	C)	Alcohol	D)	Water		
Ans	A)	SnCl ₂ and PdCl ₂				
18.		complexing agent that is used in the electro		-		
	A)	CuSO ₄	B)	NaOH		
A	C)	Formaldehyde	D)	EDTA		
Ans		D) EDTA The reducing agent that is used in the electroless plating of copper is				
20.		EDTA				
	A) C)	Formaldehyde	B) D)	K ₂ Cr ₂ O ₇		
Ano			(ט	NOI		
Ans		C) Formaldehyde During electroless plating, copper will undergo reaction				
21.		Reduction		Oxidation		
	A)		B)			
A 10.0	C)	Substitution	D)	Neutralization		
Ans 22	B)	Buffer which is used in the electroless plating of copper is				
		NH4OH-NH4Cl		CuSO ₄ -CuCl ₂		
	A) C)	NaOH-NaCl	B)	NaOH-Rochelle salt		
Ana	D)	NaOH-NaCi NaOH-Rochelle salt	ען)	INAUTI-NUCTICIE SAIL		
Ans 23.			ross	tion occurring on a protracted active curfees		
23.		roless plating is driven by the Autocatalytic oxidation	B)	tion occurring on a pretreated active surface. Autocatalytic redox		
-	A) C)	Autocatalytic eduction	D)	Autocatalytic redox Autocatalytic displacement		
Ans		Autocatalytic redox	ט)	Autocatalytic displacement		
	LOI	- AUIVGIGIVIII, IEUVA				

24.	1 nm =				
	A)	10 ⁻⁷ m	B)	10 ⁻⁹ m	
	C)	10 ⁹ m	D)	10 ⁻³ m	
Ans	B) 10 ⁻⁹ m				
25.	Materials having two dimensions in the nanoscale are called nanomaterials				
	A)	Zero Dimensional	B)	One Dimensional	
	C)	Two Dimensional	D)	Three Dimensional	
Ans	B)	One Dimensional			
26.	An e	xample of zero-dimensional nanomaterials	<u>is</u>		
	A)	Nanosheets	B)	Nanotubes	
	C)	Nanospheres	D)	Nanowires	
Ans	C) Nanospheres				
27.		xample of one-dimensional nanomaterials is	<u>s</u>		
	A)	Nanosheets	B)	Nanoplates	
	C)	Nanospheres	D)	Nanowires	
Ans	D)	Nanowires			
28.	An example of two-dimensional nanomaterials is				
	A)	Nanosheets	B)	Nanotubes	
	C)	Nanospheres	D)	Nanowires	
Ans	A)	Nanosheets			
29.		ose the INCORRECT statement for the sol-g			
	A)	Sol is a stable suspension of colloidal	B)	Metal alkoxides are the preferred precursors in	
		particles in a liquid		sol-gel process	
	C)	Urea is used as fuel	D)	The gel is formed by the polymerization reaction	
Ans	C)	Urea is used as fuel			
30.	Which is the preferred precursor in the sol-gel method?				
	A)	Metal chlorides	B)	Metal nitrates	
	C)	Metal hydroxides	D)	Metal alkoxides	
Ans	D)	Metal alkoxides			
31.	CVD	stands for			
	A)	Carbon Vapor Dissolution	B)	Chemical Vapor Deposition	
	C)	Carbon Vapor Deposition	D)	Chemical Vapor Dissolution	
Ans	B)	Chemical Vapor Deposition			
32.		is the carbon source used in the synthe	esis c	of carbon nanotubes by CVD technique.	
	A)	Nitrogen gas	B)	Argon gas	
	C)	Hydrocarbon gas	D)	Hydrogen gas	
Ans	C)	Hydrocarbon gas	/	, , , , , , , , , , , , , , , , , , ,	
	-,				

Memory Devices & Display Systems

33.	Whi	Which of the following is a permanent memory in the computer?			
	A)	RAM	B)	ROM	
	C)	CPU	D)	CD ROM	
Ans	B)	ROM			
34.	The information recorded on EEPROM is erased using:				
	A)	Ultraviolet light	B)	Electrical signals	
	C)	Sunlight	D)	Infrared radiation	
Ans	B)	Electrical signals			
35.	Whi	Which among the following is a Flash memory device?			
	A)	Hard Disc Drive (HDD)	B)	CD Drive	
	C)	RAM	D)	USB drive	
Ans	D)	D) USB drive			
36.	The	The full form of EPROM is			
	A)	Easy Programmable Read-Only Memory	B)	Erasable Programmable Read-Only Memory	

	C)	Eradicate Programmable Read-Only	D)	Electrically Programmable Read-Only Memory		
	Β,	Memory				
Ans	,	B) Erasable Programmable Read-Only Memory				
37.		full form of PROM is				
	A)	Previous Read-Only Memory	B)	Programmable Read-Out Memory		
	C)	Programmable Read-Only Memory	D)	Permanent Read-Only Memory		
Ans	C)	Programmable Read-Only Memory				
38.		xample for a non-volatile memory device is				
	A) C)	SPRAM RAM	B)	ROM RRAM		
Ano	B)	ROM	(ט	RRAIVI		
Ans 39.		ା KOM ch among the following memory used in a d	iaita	L camara?		
39.	A)	Virtual memory	B)	Flash Memory		
	C)	Main Memory	D)	Cache Memory		
Ans	B)	Flash Memory	D)	Cache Memory		
40.	_	l is defined as				
 0.	A)	Read Out Memory	B)	Read Once Memory		
	C)	Read Only Memory	D)	Read One Memory		
Ans	C)	Read Only Memory	(U)	Tread One Memory		
41.		t is the full form of RAM?				
71.	A)	Read Access Memory	B)	Readable Access Memory		
	C)	Random Accumulator Memory	D)	Random Access Memory		
Ans	D)	Random Access Memory	(ט	Trandom Access Memory		
42.		ch computer memory chip allows simultane	OII6	hoth read and write operations?		
72.	A)	ROM	B)	RAM		
	C)	PROM	D)	EEPROM		
Ans	_		, D)	-		
Ans 43.	B)	RAM				
Ans 43.	B) In w		lata	is written, it cannot be changed?		
	B)	RAM hich type of memory, once the program or c				
	B) In wi	RAM hich type of memory, once the program or o PROM	lata i	is written, it cannot be changed?		
43.	B) In w A) C) A)	RAM hich type of memory, once the program or o PROM EEPROM	lata i B) D)	is written, it cannot be changed? EPROM Flash		
43.	B) In w A) C) A)	RAM hich type of memory, once the program or o PROM EEPROM PROM	lata i B) D)	is written, it cannot be changed? EPROM Flash		
43.	B) In wi A) C) A) Whice	RAM hich type of memory, once the program or of PROM EEPROM PROM PROM ch type of ROM is used for erasing purposes	lata i B) D)	is written, it cannot be changed? EPROM Flash		
43.	B) In wide A) C) A) Whice A)	RAM hich type of memory, once the program or of PROM EEPROM PROM PROM ch type of ROM is used for erasing purposes Flash	lata B) D) s onl	is written, it cannot be changed? EPROM Flash Iy? WROM		
43. Ans 44.	B) In wl A) C) A) Which C) C) In wl	RAM hich type of memory, once the program or of PROM EEPROM PROM ch type of ROM is used for erasing purposes Flash EEPROM EEPROM EEPROM hich type of ROM, data can be erased by ult	B) D) s onl B) D)	is written, it cannot be changed? EPROM Flash Iy? WROM		
43. Ans 44.	B) In will A) C) A) White A) C) C) In will or m	RAM hich type of memory, once the program or of PROM EEPROM PROM ch type of ROM is used for erasing purposes Flash EEPROM EEPROM hich type of ROM, data can be erased by ultranufacturer?	B) S on D)	is written, it cannot be changed? EPROM Flash ly? WROM PROM PROM Diet light and then reprogrammed by the user		
43. Ans 44.	B) In w A) C) A) Which A) C) C) In w or m A)	RAM hich type of memory, once the program or of PROM EEPROM PROM ch type of ROM is used for erasing purposes Flash EEPROM EEPROM hich type of ROM, data can be erased by ulteranufacturer? EPROM	B) S on B) D) ravid	is written, it cannot be changed? EPROM Flash ly? WROM PROM Diet light and then reprogrammed by the user EEPROM		
43. Ans 44. Ans 45.	B) In wl A) C) A) Whice A) C) In wl or m A) C)	RAM hich type of memory, once the program or of PROM EEPROM PROM ch type of ROM is used for erasing purposes Flash EEPROM EEPROM hich type of ROM, data can be erased by ultanufacturer? EPROM PROM PROM	B) S on D)	is written, it cannot be changed? EPROM Flash ly? WROM PROM PROM Diet light and then reprogrammed by the user		
43. Ans 44. Ans 45.	B) In w A) C) A) Whice A) C) In w or m A) C) A)	RAM hich type of memory, once the program or of PROM EEPROM PROM ch type of ROM is used for erasing purposes Flash EEPROM EEPROM hich type of ROM, data can be erased by ulteranufacturer? EPROM PROM PROM PROM EPROM PROM EPROM	B) S on B) D) ravid	is written, it cannot be changed? EPROM Flash ly? WROM PROM Diet light and then reprogrammed by the user EEPROM		
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43. Ans 44. Ans 45. Ans 46.	B) In wl A) C) A) Whice A) C) In wl or m A) C) A) The A) C) B) An e A) C) B) Whice	PROM EEPROM PROM EEPROM EN type of ROM is used for erasing purposes Flash EEPROM EEPROM EEPROM EEPROM hich type of ROM, data can be erased by ulteranufacturer? EPROM PROM PROM EPROM Full form of EEPROM is Easy Erasable Programmable Read-Only Memory Easy Eradicate Programmable Read-Only Memory Electrically Erasable Programmable Read-Only Memory Electrically Erasable Programmable Read-Only Memory Electrically Erasable Programmable Read-Only Memory Read Only Memory Read Only Memory Read Only Memory Random Access Memory ch of the following is a popular type of trans	B) D) ravio B) D) Only B) D)	is written, it cannot be changed? EPROM Flash Iy? WROM PROM PROM Det light and then reprogrammed by the user EEPROM WROM WROM Electrically Erasable Programmable Read Only Memory Electrically Easy Programmable Read-Only Memory Memory Memory Random Access Memory Flash Memory r-type memory?		
43. Ans 44. Ans 45. Ans 46. Ans	B) In w A) C) A) C) In w or m A) C) A) The A) C) B) An e A) C) B)	RAM hich type of memory, once the program or of PROM EEPROM PROM ch type of ROM is used for erasing purposes Flash EEPROM hich type of ROM, data can be erased by ultanufacturer? EPROM PROM PROM PROM EPROM Full form of EEPROM is Easy Erasable Programmable Read-Only Memory Easy Eradicate Programmable Read-Only Memory Electrically Erasable Programmable Read example of a volatile memory device is Hybrid Memory Read Only Memory Read Only Memory Random Access Memory	B) D) ravid B) D) Only B) D)	EPROM Flash Ny? WROM PROM PROM Det light and then reprogrammed by the user EEPROM WROM Electrically Erasable Programmable Read Only Memory Electrically Easy Programmable Read-Only Memory Memory Memory Random Access Memory Flash Memory		

49.	Which property of polymers makes them suitable for applications in memory devices?				
	A)	High electrical resistance	B)	Low thermal stability	
	C)	Bistable state	D)	Brittle nature	
Ans	C)	Bistable state			
50.	tals?				
	A)	Nematic	B)	Isotropic	
	C)	Smectic	D)	Amorphous	
Ans	D) Amorphous				
51.	Mes	sophase refers to:			
	A)	Solid state	B)	Liquid state	
	C)	Liquid crystal state	D)	Gaseous state	
Ans	C)	Liquid crystal state			
52.	Liquid crystals are usually composed of				
	A)	Coil-like molecules	B)	Rod-like molecules	
	C)	Oval molecules	D)	Triangular molecules	
Ans	B)	Rodlike molecules			
53.	Whi	ch phase of liquid crystals constitute molec	ules	having twisted helical structure?	
	A)	Nematic	B)	Isotropic	
	C)	Smectic	D)	Cholesteric	
Ans	D)	Cholesteric			
54.	Liquid crystal displays (LCDs) work based on the principle of:				
	A)	Electromagnetic induction	B)	Electrochemical reactions	
	C)	Opto-electronic effect	D)	Liquid crystal polarization	
Ans	C)	Opto-electronic effect			
55.	Whi	ch of the following phases of liquid crystals	has		
	A)	Smectic	B)	Nematic	
	C)	Cholesteric	D)	Isotropic	
Ans	A)	Smectic			
56.	Which property of liquid crystals makes them suitable for display technologies?				
	A)	High electrical conductivity	B)	Low viscosity	
	C)	Low melting point	D)	Optical anisotropy	
Ans	D)	Optical anisotropy			
57.	The orientational behaviour of lyotropic crystals is a function of				
	A)	Concentration	-	Solvent	
	C)	Concentration and solvent	D)	Neither concentration nor solvent	
Ans		C) Concentration and solvent			
58.		full form of LEC is	1	I	
	A)	Light-emitting Electrochemical Cell	B)	Liquid-emitting Electromagnetic Cell	
_	C)	Light-emitting Electrical Cell	D)	Light-emitting Electronic Cell	
Ans	A)	Light-emitting Electrochemical Cell			
